Photomask Japan 2015: Photomask and Next-Generation Lithography Mask Technology XXII

Nobuyuki Yoshioka
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Contents

vii *Authors*
xi *Conference Committees*

FPD PHOTOMASKS

9658 02 **Photomasks for FPD (Invited Paper)** [9658-26]

9658 03 **Impact of the back side flatness of a mask on the panel overlay** [9658-34]

DSA

9658 04 **N7 logic via patterning using templated DSA: implementation aspects** [9658-37]

WRITING TECHNOLOGIES

9658 05 **Investigation of local registration performance of IMS Nanofabrication's Multi-Beam Mask Writer** [9658-36]

PHOTOMASK FABRICATION PROCESSES

9658 06 **The method of quartz damage recovery in the photomask repair process** [9658-24]

9658 07 **Multi-beam SEM technology for ultra-high throughput** [9658-30]

9658 08 **Development of high-transmittance phase-shifting mask for ArF immersion lithography** [9658-64]

MDP & OPC

9658 0A **Pitch-based pattern splitting for 1D layout** [9658-9]

9658 0B **High performance ILT for hotspots repair with hierarchical pattern matching** [9658-13]

9658 0C **Challenges and requirements of mask data processing for multi-beam mask writer** [9658-60]

EUVL MASKS I

9658 0E **Mask blank defect printability comparison using optical and SEM mask and wafer inspection and bright field actinic mask imaging** [9658-63]

EUVL MASKS II

9658 0F **EUV scanner printability evaluation of natural blank defects detected by actinic blank inspection** [9658-52]

9658 0G **ENDEAVOUR to understand EUV buried defect printability** [9658-57]

9658 0H **Defectivity evaluation of EUV reticles with etched multilayer image border by wafer printing analysis** [9658-53]

9658 0I **Alternative EUV mask technology to compensate for mask 3D effects** [9658-40]

EUVL MASKS III

9658 0J **Grid-supported EUV pellicles: A theoretical investigation for added value** [9658-46]

9658 0K **Impact of deformed extreme-ultraviolet pellicle in terms of CD uniformity** [9658-55]

EUVL MASKS IV

9658 0L **Patterned mask inspection technology with Projection Electron Microscope (PEM) technique for 11 nm half-pitch (hp) generation EUV masks** [9658-39]

9658 0M **Pattern inspection of etched multilayer EUV mask** [9658-47]

9658 0N **Analysis of a low-aspect phase defect for actinic EUVL mask blank inspection** [9658-48]

9658 0O **Detection capability of Actinic Blank Inspection tool** [9658-42]

POSTER SESSION

9658 0P **Development of new high transmission eaPSM for Negative Tone Development process on wafer** [9658-50]

9658 0Q **The study of develop optimization to control various resist defect in Photomask fabrication** [9658-25]

9658 0R **Study on modeling of resist heating effect correction in EB mask writer EBM-9000** [9658-61]

9658 0S **Mask CD uniformity improvement by electron scanning exposure based Global Loading Effect Correction** [9658-21]

9658 0T **Maskless lithography using point array technique for fine patterns** [9658-14]

9658 0U **Grab a coffee: your aerial images are already analyzed** [9658-38]

9658 0V **Study of defect verification based on lithography simulation with a SEM system** [9658-51]

9658 0W **Improvements of AIMS D2DB matching for product patterns** [9658-49]

9658 0X **Automatic classification and accurate size measurement of blank mask defects** [9658-58]

9658 0Y **Strategy optimization for mask rule check in wafer fab** [9658-18]

9658 0Z **CD measurement point extraction from local dense patterns** [9658-28]

9658 10 **Effective conflict resolution strategies for SRAF placement** [9658-22]

9658 11 **Exploring EUV mask backside defectivity and control methods** [9658-45]

9658 12 **Influence of unit process interaction on EUV mask performance** [9658-29]

9658 13 **Patterning dependence on the mask defect for extreme ultraviolet lithography** [9658-54]

9658 14 **Mo/Si multilayer mirrors with 300-bilayers for EUV lithography** [9658-43]

SPECIAL POSTER SESSION: MASK/LITHOGRAPHY RELATED TECHNOLOGY IN ACADEMIA

9658 15 **Investigation into causes of resolution degradation in projection exposure using a gradient-index lens array** [9658-19]

9658 16 **Fabrication of microfluidic paths using thick and vertical resist patterns printed by exposure with intentional large defocus** [9658-16]

9658 17 **Readability of intentionally degraded two dimensional code marks printed lithographically using a squared optical fiber matrix** [9658-11]

9658 18 **EUV mask observations using a coherent EUV scatterometry microscope with a high-harmonic-generation source** [9658-27]

9658 19 **Development of a reflectometer for a large EUV mirror in NewSUBARU** [9658-59]

9658 1A **Experimental observation of laser-produced Sn extreme ultraviolet source diameter for high-brightness source** [9658-5]

9658 1B **Evaluation of a dot target based high-brightness microplasma extreme ultraviolet (EUV) source by hydrodynamic simulation** [9658-6]

9658 1C **Dynamics of radical ions of fluorinated polymer for Extreme Ultraviolet (EUV) lithography** [9658-23]

Authors

Numbers in the index correspond to the last two digits of the six-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first four digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Adachi, Takashi, 0P
Ahn, Won-suk, 08
Akima, Shinji, 0G
Amano, Tsuyoshi, 0L, 0M
Anze, Hirohito, 0R
Arai, Goki, 1A, 1B
Arias Espinoza, Juan Diego, 0J
Axelrad, Valery, 0A
Badger, Karen, 0G
Bang, Ju-Mi, 08
Barouch, Eytan, 0K, 13
Bekaert, J., 04
Bender, Markus, 12
Benk, Markus P., 0E
Bhamidipati, Samir, 0X
Bogers, Maurice, 0J
Bolton, Luke, 11
Bonam, Ravi, 0G, 11
Brouns, Derk, 0J
Buck, Peter, 0X
Cao, Y., 04
Chalom, Daniel, 05
Cheong, Lin, 11
Choi, Jin, 0C
Collins, Kevin, 11
Daneshpanah, Mehdi, 05
Davydova, Natalia, 0I
de Kruif, Robert, 0I
de Winter, Laurens, 0J
Deng, Erwin, 0Y
Dhalluin, Florian, 0J
Dinh, Thanh-Hung, 1A, 1B
Doise, J., 04
Eder-Kapl, Stefan, 05
Eyring, Stefan, 05
Fenger, G., 04
Fliervoet, Timon, 0I
Fujii, Nobuaki, 0V
Fujimura, Yukihiro, 0P
Fujino, Takahiro, 18
Fujiyoshi, Ryoko, 1C
Fukugami, Norihito, 0H
Gallagher, Emily, 0F, 0H
Ganjugunte, Shashidhara K., 10
Garbowski, Tomasz, 07
Garetto, Anthony, 0U
Geist, David, 05
Goldberg, Kenneth A., 0E
Gronheid, R., 04
Guo, Eric, 0S
Hara, Daisuke, 0V
Hara, Hiroyuki, 1A, 1B
Harada, Tetsuo, 18, 19
Hashimoto, Hiraku, 19
Hatakeyama, Masahiro, 0L
Hatayama, Masatoshi, 14
Hayano, Katsuya, 0P, 0V
Hendrickx, Eric, 0I
Her, Y. J., 04
Higashiguchi, Takeshi, 1A, 1B
Hirano, Ryoichi, 0L, 0M
Hirano, Termusa, 03
Horiuchi, Toshiyuki, 15, 16, 17
Hosono, Koji, 0Z
Hudek, Peter, 05
Ichimaru, Satoshi, 14
Iguchi, Haruki, 19
Iida, Susumu, 0L, 0M
Iizuka, Tetsuya, 02
Imai, Hidemichi, 0V
Ino, Tomohisa, 0N
Ishii, Hiroyuki, 0A
Isogawa, Takeshi, 0G, 11
Iwanaga, Yoshinori, 03
Iwasaki, Jun-ya, 17
Jayaram, Srividya, 10
Jeon, Chan-Uk, 08, 0C
Ji, Hye-Rim, 13
Jonckheere, Rik, 0F, 0H
Jung, HoYong, 06
Kagawa, Masayuki, 0G, 11
Kamikubo, Takashi, 0R
Kanaya, Yasuhiro, 02
Kanno, Koichi, 0V, 0W
Kato, Yasuo, 0R
Kemen, Thomas, 07
Kemmochi, Daisuke, 03
Kim, ByungJu, 0Q
Kim, Guk-Jin, 13
Kim, Hee-Bom, 08
Kim, In-Seon, 0K, 13
Kim, Ji-Young, 08
Kim, Min-Su, 13
Kim, MunSik, 06
Kim, SangPyo, 06, 0Q
Kindt, Louis, 11
Kinoshita, Hiroo, 18, 19
Kinoshita, Hiroshi, 03

Klikovits, Jan, 05
Kodera, Yutaka, 0G, 0H
Kozawa, Takahiro, 1C
Kuki, Masaki, 19
Kuribara, Masayuki, 0V
Kusunose, Haruhiko, 0O
LaCour, Pat, 10
Laske, Frank, 05
Lawliss, Mark, 0G, 11
Lee, Dong Hyun, 0C
Lee, Rachel, 0Y
Lee, SookHyun, 0C
Lentzen, Sven, 0J
Li, Rivan, 0S
Lim, JongHoon, 0Q
Lin, Roger, 0Y
Lin, Shaina, 0Y
Lu, Max, 0S
Mangat, Pawitter, 0E
Matsumoto, Hiroyuki, 0Z
Matsumoto, Jun, 0V
Matsushita, Shohei, 0V
Mikami, Koji, 0A
Miura, Yoichi, 0P
Miyai, Hiroki, 0N, 0O
Miyajima, Masaaki, 0Z
Miyashita, Hiroyuki, 0P, 0V, 0W
Miyauchi, Toru, 0Z
Miyazaki, Junji, 0I
Mori, Ichiro, 0O
Morikawa, Yasutaka, 0P
Morizane, Yuta, 16
Murakami, Takeshi, 0L
Murakawa, Tsutomu, 0V
Nagata, Yutaka, 18
Nakagawa, Takashi, 0T
Nakajima, Fumitaka, 0T
Nakamura, Takayuki, 0V
Nakayama, Ryo, 0A
Nakayamada, Noriaki, 0R
Namkung, Hoon, 06
Naoe, Mitsufumi, 0Z
Narita, Eisuke, 11
Nesládek, Pavel, 12
Neumann, Jens Timo, 0I
Nishiguchi, Masaharu, 0W
Nishimoto, Nirou, 0T
Nomura, Haruyuki, 0R
Nomura, Naoya, 1C
Ogasawara, Munehiro, 0R
Oh, Hye-Keun, 0K, 13
Ohara, Kana, 0W
Ohchi, Tadayuki, 14
Ohta, Eiji, 0T
Okamoto, Kazumasa, 1C
Oku, Satoshi, 14
Oyama, Kenichi, 0A
Pang, Linyong, 0V
Paninjath, Sankaranarayanan, 0X
Park, EuiSang, 06, 0Q
Park, Jin-Goo, 13
Park, Sinjeung, 0C
Pereira, Mark, 0X
Péter, Mária, 0J
Philipsen, Vicky, 0I
Poro, Richard, 11
Qi, Zhengqing John, 0G
Rademacher, Thomas, 0U
Rankin, Jed, 0G, 11
Roeth, Klaus-Dieter, 05
Rolff, Haiko, 12
Ruinemans, Erik, 0J
Ryckaert, J., 04
Sakajiri, Kyohei, 0B
Sakata, Yo, 0H
Satake, Masaki, 0W
Sato, Takanori, 15
Scaccabarozzi, Luigi, 0J
Schedel, Thorsten, 12
Schulz, Kristian, 0U
Seki, Kazunori, 0G
Seo, Hwan-Seok, 08
Seung, Byoung-Hoon, 08
Shi, Irene, 0S
Shida, Soichi, 0V
Shin, In Kyun, 0C
Smayling, Michael C., 0A
Smith, Daniel, 0J
Son, Donghwan, 0W
Son, JaeSik, 0Q
Song, Jae-Min, 08
Steinhartová, Tereza, 12
Strecker, Norbert, 10
Suematsu, Kenichi, 0L
Suganuma, Mizuna, 0R
Sunahara, Atsushi, 1A, 1B
Suzuki, Tomohiro, 0O
Tachikawa, Masahiro, 0T
Takagi, Noriaki, 0F
Takeda, Nobuo, 0T
Takehisa, Kiwamu, 0O
Takeuchi, Kanji, 0Z
Tamamushi, Shuichi, 0C
Tanaka, Yusuke, 18
Tani, Ayako, 0P
Terao, Kenji, 0L
Tian, Eric, 0S
Tolani, Vikram, 0W
Tomooka, Takatoshi, 02
Torunoglu, Ilhami, 10
Tsujita, Koichiro, 0A
Turley, Christina, 11
Umegaki, Kikuo, 1C
Van den Heuvel, Dieter, 0F
Van der Sanden, Jack, 0J
Van der Zande, Wim, 0J
Van Gils, Rob, 0J
Van Look, Lieve, 0I
van Oosten, Anton, 0I
van Schoot, Jan, 0I

Vandenberghe, Geert, 04, 0I
Verduijn, Erik, 0E, 0H
Vermeulen, Hans, 0J
Wang, Alice, 0Y
Watanabe, Genta, 0H
Watanabe, Hidehiro, 0F, 0L, 0M, 0O
Watanabe, Jun, 17
Watanabe, Takeo, 18, 19
Wittebrood, Friso, 0I
Wojdyla, Antoine, 0E
Wood, Obert R., II, 0E
Yaegashi, Hidetami, 0A
Yamamoto, Hiroki, 1C
Yamane, Takeshi, 0N
Yang, Chuen Huei, 0Y
Yashima, Jun, 0R
Yeung, Micheal, 0K, 13
Yim, DongGyu, 06, 0Q
Yoshikawa, Shingo, 0P, 0V
Yoshikawa, Shoji, 0L
Yoshikawa, Yutaka, 03
Zeidler, Dirk, 07

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Frank E. Abboud, Intel Corporation (United States)

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Kokoro Kato, Hitachi High-Tech Science Corporation (Japan)
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